Amplifier Transistors

NPN Silicon

Features

• Pb–Free Packages are Available*

MAXIMUM RATINGS

Rating		Symbol	Value	Unit
	2N5088 2N5089	V _{CEO}	30 25	Vdc
	2N5088 2N5089	V _{CBO}	35 30	Vdc
Emitter – Base Voltage		V_{EBO}	3.0	Vdc
Collector Current – Continuous		Ι _C	50	mAdc
Total Device Dissipation @ $T_A = 25^{\circ}C$ Derate above $25^{\circ}C$		PD	625 5.0	mW mW/°C
Total Device Dissipation @ $T_C = 25$ Derate above 25°C	5°C	PD	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range		T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	°C/W

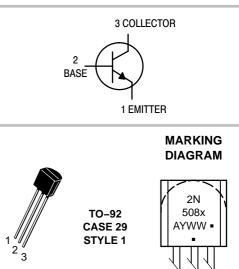
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. $R_{\theta,JA}$ is measured with the device soldered into a typical printed circuit board.



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ORDERING INFORMATION

Device	Package	Shipping [†]			
2N5088	TO-92	5000 Units/Box			
2N5088G	TO–92 (Pb–Free)	5000 Units/Box			
2N5088RLRA	TO-92	2000/Tape & Reel			
2N5088RLRAG	TO–92 (Pb–Free)	2000/Tape & Reel			
2N5089	TO-92	5000 Units/Box			
2N5089G	TO–92 (Pb–Free)	5000 Units/Box			
2N2089RLRA	TO-92	2000/Tape & Reel			
2N2089RLRAG	TO–92 (Pb–Free)	2000/Tape & Reel			
2N2089RLRE	TO-92	2000/Tape & Reel			
2N2089RLREG	TO–92 (Pb–Free)	2000/Tape & Reel			

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic		Symbol	Min	Мах	Unit
OFF CHARACTERISTICS			-		
Collector – Emitter Breakdown Voltage (Note 2) $(I_C = 1.0 \text{ mAdc}, I_B = 0)$	2N5088 2N5089	V _{(BR)CEO}	30 25		Vdc
Collector – Base Breakdown Voltage $(I_C = 100 \ \mu Adc, I_E = 0)$	2N5088 2N5089	V _{(BR)CBO}	35 30		Vdc
Collector Cutoff Current $(V_{CB} = 20 \text{ Vdc}, I_E = 0)$ $(V_{CB} = 15 \text{ Vdc}, I_E = 0)$	2N5088 2N5089	I _{CBO}		50 50	nAdc
		I _{EBO}		50 100	nAdc
ON CHARACTERISTICS					
DC Current Gain ($I_C = 100 \ \mu Adc, V_{CE} = 5.0 \ Vdc$)	2N5088 2N5089	h _{FE}	300 400	900 1200	_
(I _C = 1.0 mAdc, V _{CE} = 5.0 Vdc)	2N5088 2N5089		350 450		
(I _C = 10 mAdc, V_{CE} = 5.0 Vdc) (Note 2)	2N5088 2N5089		300 400		
Collector – Emitter Saturation Voltage ($I_C = 10 \text{ mAdc}$, $I_B = 1.0 \text{ mAdc}$)		V _{CE(sat)}	-	0.5	Vdc
Base – Emitter On Voltage ($I_C = 10 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc}$) (Note 2)		$V_{BE(on)}$	-	0.8	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain – Bandwidth Product ($I_C = 500 \ \mu Adc, V_{CE} = 5.0 \ Vdc, f = 20 \ MHz$)		f _T	50	-	MHz
Collector-Base Capacitance ($V_{CB} = 5.0 \text{ Vdc}, I_E = 0, f = 1.0 \text{ MHz}$)		C _{cb}	-	4.0	pF
Emitter–Base Capacitance ($V_{EB} = 0.5 \text{ Vdc}, I_C = 0, f = 1.0 \text{ MHz}$)		C _{eb}	_	10	pF
Small–Signal Current Gain (I _C = 1.0 mAdc, V _{CE} = 5.0 Vdc, f = 1.0 kHz)	2N5088 2N5089	h _{fe}	350 450	1400 1800	_
Noise Figure (I _C = 100 μ Adc, V _{CE} = 5.0 Vdc, R _S = 1.0 kΩ, f = 1.0 kHz)	2N5088 2N5089	NF		3.0 2.0	dB

2. Pulse Test: Pulse Width \leq 300 µs, Duty Cycle \leq 2.0%.

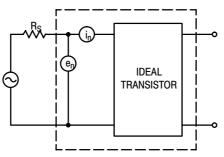


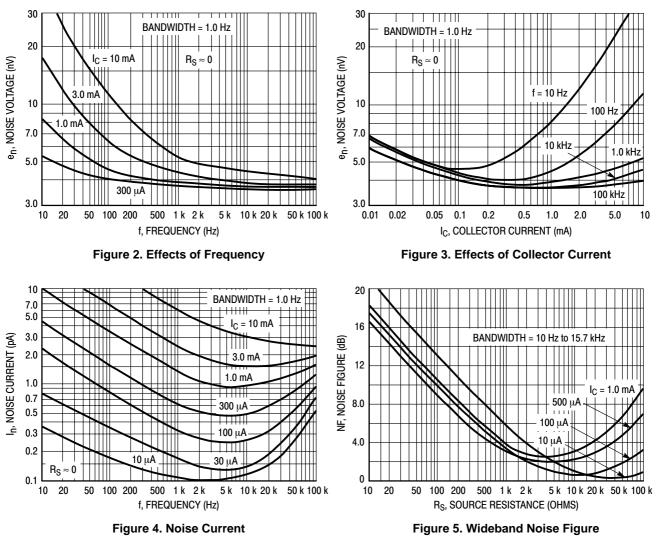
Figure 1. Transistor Noise Model

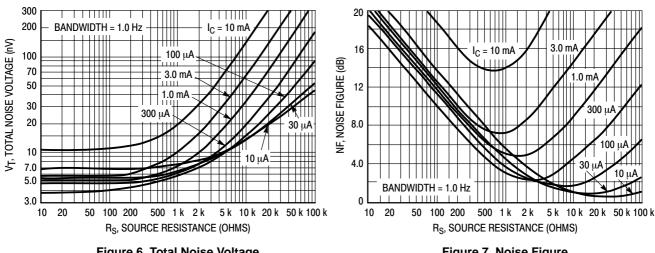
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NOISE CHARACTERISTICS

 $(V_{CE} = 5.0 \text{ Vdc}, T_A = 25^{\circ}C)$

NOISE VOLTAGE



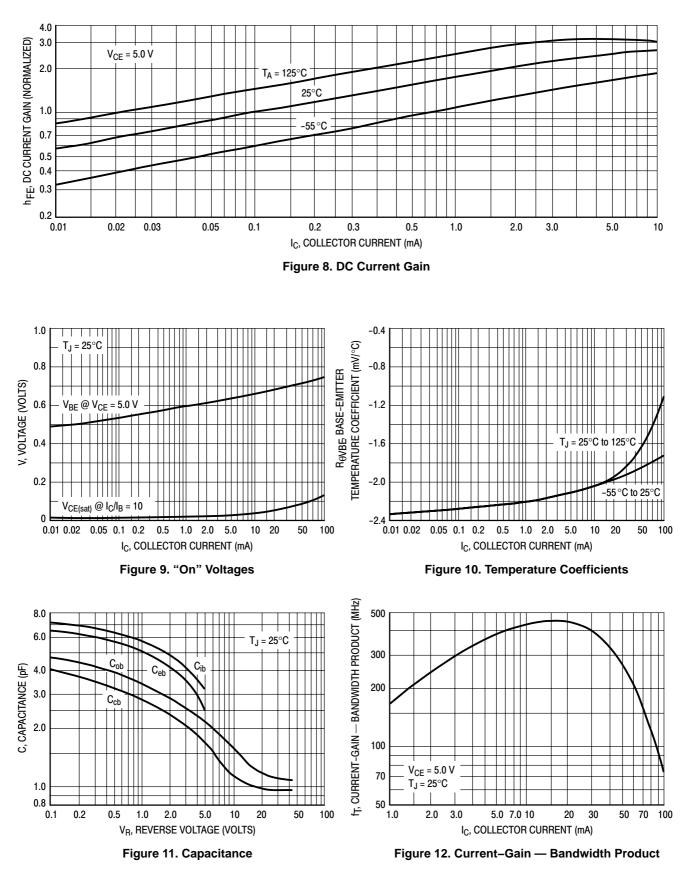


100 Hz NOISE DATA

Figure 6. Total Noise Voltage

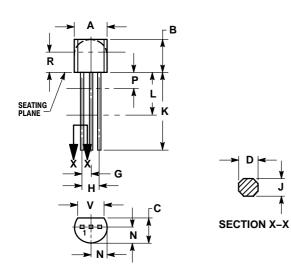


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PACKAGE DIMENSIONS

TO-92 **TO-226AA** CASE 29-11 **ISSUE AL**



NOTES

- DIMENSIONING AND TOLERANCING PER ANSI 1. Y14.5M, 1982. CONTROLLING DIMENSION: INCH.
- 2. 3.
- CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
- LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM. 4.

	INCHES		MILLIMETER		
DIM	MIN	MAX	MIN	MAX	
Α	0.175	0.205	4.45	5.20	
В	0.170	0.210	4.32	5.33	
С	0.125	0.165	3.18	4.19	
D	0.016	0.021	0.407	0.533	
G	0.045	0.055	1.15	1.39	
Н	0.095	0.105	2.42	2.66	
J	0.015	0.020	0.39	0.50	
Κ	0.500		12.70		
L	0.250		6.35		
Ν	0.080	0.105	2.04	2.66	
Ρ		0.100		2.54	
R	0.115		2.93		
٧	0.135		3.43		

STYLE 1: PIN 1. EMITTER BASE 2 COLLECTOR 3.

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